

Form PTO-1449

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PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.  
MI22-1951PRIORITY SERIAL NO.  
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## U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
UH	AA	5,256,455	10/26/93	Numasawa			
	AB	5,459,635	10/17/95	Tomozawa et al.			
	AC	5,596,214	01/21/97	Endo			
	AD	5,618,761	04/08/97	Eguchi et al.			
	AE	5,731,948	03/24/98	Yializis et al.			
	AF	5,776,254	07/07/98	Yuuki et al.			
	AG	5,783,253	07/21/98	Roh			
	AH	5,798,903	8/25/98	Dhote et al.			
	AI	6,043,526	3/28/00	Ochiai			
	AJ	6,046,345	04/04/00	Kadokura et al.			
MR	AK	6,078,492	06/20/00	Huang et al.			

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		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
YB	AL	EP 0 855 735 A2	29.07.98	Europe (Applied Materials, Inc.)				
	AM	EP 0 957 522 A2	17.11.99	Europe (Matsushita Electric Industrial Co. Ltd.)				
	AN	WO 98/39497	09/11/98	WIPO (Simpson, et al.)				
	AO	0 474 140 A1	08/30/91	Europe (Kamiyama)				
YH	AP	WO 99/64645	12/16/99	WIPO (Narwankar, et al.)				

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YH	AR	Steve Bilodeau et al., <i>Composition Dependence of the Dielectric Properties of MOCVD Ba<sub>1-x</sub>Sr<sub>x</sub>TiO<sub>3</sub></i> , pp. 1-21 (MRS Fall Meeting 12/01/94).
	AS	Steve M. Bilodeau et al., <i>MOCVD BST for High Density DRAM Applications</i> (Preprint for SEMICON/WEST 07/12/95), 2 pages.
YH	AT	Y-C Choi et al., Abstract, <i>Improvements of the Properties of Chemical-Vapor-Deposited (Ba,Sr)TiO<sub>3</sub> Films Through Use of a Seed Layer</i> , 36 J. PN. J. APPL. PHYS. Pt. 1, No. 11, pp. 6824-6828 (1997)

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YB	AA	6,153,898	11/28/00	Watanabe et al.			
	AB	6,037,205	03/14/00	Huh, et al.			
	AC	5,470,398	11/28/95	Shibuya, et al.			
	AD	5,254,505	10/19/93	Kamiyama			
	AE	6,156,638	12/05/00	Agarwal et al.			
YB	AF	6,165,834	12/26/00	Agarwal et al.			
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YB	AR	Chung Ming Chu et al., Abstract, <i>Electrical properties and crystal structure of (Ba,Sr)TiO<sub>3</sub> films prepared at low temperatures on a LaNiO<sub>3</sub> electrode by radio-frequency magnetron ...</i> , 70 A PPLIED PHYSICS LETTERS No. 2, pp. 249-251 (1997).
YB	AS	Kazuhiro Eguchi et al., Abstract, <i>Chemical vapor deposition of (Ba,Sr)TiO<sub>3</sub> thin films for application in gigabit scale dynamic random access memories</i> , 141 INTEGRATED FERROELECTRICS Nos. 1-4, Pt. 1, pp. 33-42 (1997).
YB	AT	Q.X. Jia et al., Abstract, <i>Structural and dielectric properties of Ba<sub>0.5</sub>Sr<sub>0.5</sub> thin films with an epi-RuO<sub>2</sub> bottom electrode</i> , 191 INTEGRATED FERROELECTRICS Nos. 1-4, pp. 111-119 (1998).

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6/14/02

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yq	AR		Takaaki Kawahara et al., <i>(Ba, Sr)TiO<sub>3</sub> Films Prepared by Liquid Source Chemical Vapor Deposition on Ru Electrodes</i> , 35 J. PN. J. APPL. PHYS. Pt. 1, No. 9B, pp. 4880, 4883 (1996).
	AS		Rajesh Khamankar et al., <i>A Novel Low-Temperature Process for High Dielectric Constant BST Thin Films for ULSI DRAM Applications</i> , Microelectronics Research Center, Univ. of Texas at Austin, TX (Undated), 2 pages.
ym	AT		Yong Tae Kim et al., Abstract, <i>Advantages of RuO<sub>2</sub> bottom electrode in the dielectric and leakage characteristics of (Ba,Sr)TiO<sub>3</sub> capacitor</i> , 35 J. PN. J. APPL. PHYS. Pt. 1, No. 12A, pp. 6153-6156 (1996).

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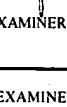
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	AR		S.H. Paek et al., Abstract, <i>Characterization of MIS capacitor of BST thin films deposited on Si by RF magnetron sputtering</i>
			Ferroelectric Thin Films V. Symposium, San Francisco, CA, pp. 33-38 (April 7, 1995).
	AS		N. Takeuchi et al., Abstract, <i>Effect of firing atmosphere on the cubic-hexagonal transition in Ba<sub>0.98</sub>Sr<sub>0.02</sub>TiO<sub>3</sub></i> , 98 N IPPON
			SERAMIKKUSU KYOKAI GAKUJUTSU RONBUNSHI No. 8, pp. 836-839 (1990).
	AT		H. Yamaguchi, et al., Abstract, <i>Reactive coevaporation synthesis and characterization of SrTiO<sub>3</sub>-BaTiO<sub>3</sub> thin films</i> , IEEE
			International Symposium on Applications of Ferroelectrics, Greenville, SC, pp. 285-288 (August 2, 1992).

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	AR	S. Yamamichi et al., Abstract, <i>Ba + Sr/Ti ratio dependence of the dielectric properties for (Ba<sub>0.5</sub>Sr<sub>0.5</sub>TiO<sub>3</sub>) thin films prepared by ion beam sputtering</i> , 64 A PPLIED PHYSICS LETTERS No. 13, pp. 1644-1646 (1994).
	AS	M. Yamamuka et al., Abstract, <i>Thermal-Desorption Spectroscopy of (Ba,Sr)TiO<sub>3</sub> Thin-Films Prepared by Chemical-Vapor-Deposition</i> , 35 JPN. J. OF APPL. PHYS. Pt. 1, No. 2A, pp. 729-735 (1996).
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<i>g</i>	AB	09/476,516		Basceri			January 3, 2000
<i>g</i>	AC	09/580,733		Basceri			May 26, 2000
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<i>g</i>	AR		Kim, et al.: "Structural and Electrical Properties. . ." Applied Physics Letters, US, American Institute of Physics Vol. 65, No. 15, 10/10/94,
			Pgs. 1955 - 1957.
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yle	AA	5,834,060	11/98	Kawahara et al.			
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mu	AR		Basceri, Cem et al., "The Dielectric Response as a Function of Temperature and Film Thickness of Fiber-Textured (Ba,Sr)TiO <sub>3</sub> Thin Films Grown by Chemical Vapor Deposition", J. Appl. Phys. 82(5), Sept. 1, 1997, pp. 2497-2504.
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	AB	App. SN 09/776,217 (as filed and amended)		C. Basceri			02/02/01
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